-100V 38mΩ P-Ch Power MOSFET

Features

- Low On-Resistance
- Excellent Gate Charge x $R_{DS(ON)}$ Product (FOM)
- Pb-Free Lead Plating
- RoHS and Halogen-Free Compliant
- 100% UIS Tested, 100% R_g Tested

Product Summary

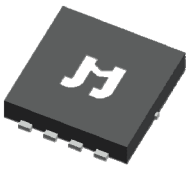
Parameter	Value	Unit
V_{DS}	-100	V
$V_{GS(th)\_Typ}$	-2.0	V
I_D (@ V_{GS} = -10V) (1)	-26	A
$R_{DS(ON)\_Typ}$ (@ V_{GS} = -10V)	38	mΩ
$R_{DS(ON)\_Typ}$ (@ V_{GS} = -4.5V)	51	mΩ

Applications

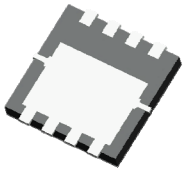
- Battery Management
- DC/DC in Telecoms and Inductrial
- Hard Switching and High Speed Circuit

PDFN3x3-8L

Top View

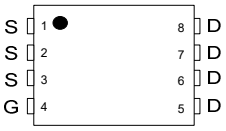


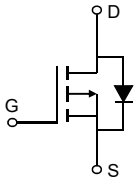
Bottom View



Pin Configuration

Top View



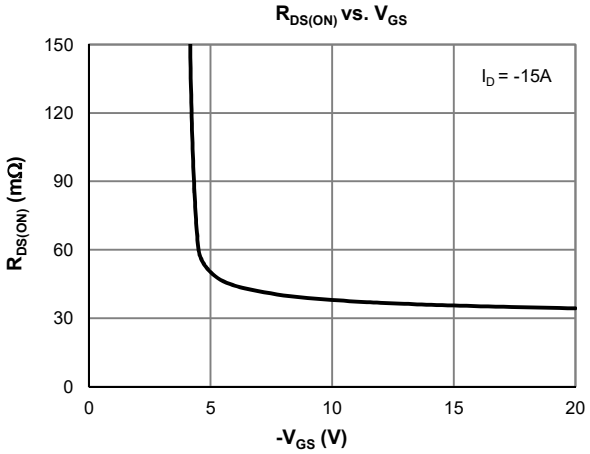


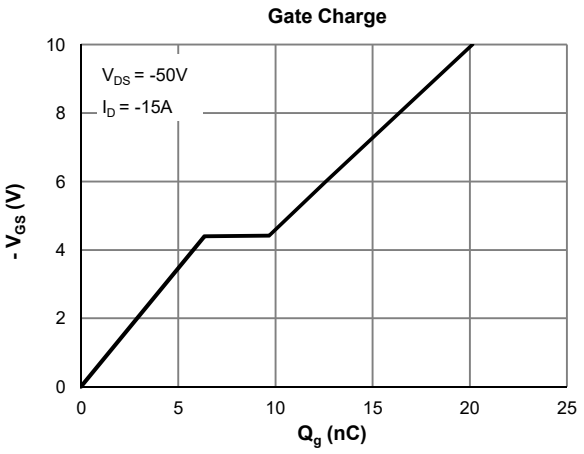
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMPL1050AU-13	PDFN3x3-8L	8	PL1050A	1	-55 to 150	13-inch Reel	5000

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	-100	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (1)	T_C = 25°C	I_D	-26	A
	T_C = 100°C		-16	
Pulsed Drain Current (2)		I_{DM}	-77	A
Avalanche Current (3)		I_{AS}	-27	A
Avalanche Energy (3)		E_{AS}	109	mJ
Power Dissipation (4)	T_C = 25°C	P_D	69	W
	T_C = 100°C		28	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C





Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = -250μA, V_{GS} = 0V	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -80V, V_{GS} = 0V			-1.0	μA
		T_J = 55°C			-5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-2.0	-3.0	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = -10V, I_D = -15A		38	50	mΩ
		V_{GS} = -4.5V, I_D = -10A		51	66	mΩ
Forward Transconductance	g_{FS}	V_{DS} = -5V, I_D = -15A		30		S
Diode Forward Voltage	V_{SD}	I_S = -1A, V_{GS} = 0V		-0.7	-1.0	V
Diode Continuous Current	I_S	T_C = 25°C			-69	A
DYNAMIC PARAMETERS [5]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -50V, f = 1MHz		1412		pF
Output Capacitance	C_{oss}			222		pF
Reverse Transfer Capacitance	C_{rss}			2.6		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz		10.2		Ω
SWITCHING PARAMETERS [5]						
Total Gate Charge (@ V_{GS} = -10V)	Q_g	V_{GS} = 0 to -10V V_{DS} = -50V, I_D = -15A		20		nC
Total Gate Charge (@ V_{GS} = -6.0V)	Q_g			12.6		nC
Gate Source Charge	Q_{gs}			6.4		nC
Gate Drain Charge	Q_{gd}			3.3		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = -10V, V_{DS} = -50V R_L = 3.3Ω, R_{GEN} = 6Ω		10.7		ns
Turn-On Rise Time	t_r			56		ns
Turn-Off DelayTime	$t_{D(off)}$			45		ns
Turn-Off Fall Time	t_f			81		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = -15A, dI_F/dt = -100A/μs		51		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = -15A, dI_F/dt = -100A/μs		130		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	47	55	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.4	1.8	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 150°C.
3. This single-pulse measurement was taken under the following condition [L = 300μH, V_{GS} = -10V, V_{DD} = -50V] while its value is limited by T_{J_Max} = 150°C.
4. The power dissipation P_D is based on T_{J_Max} = 150°C.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

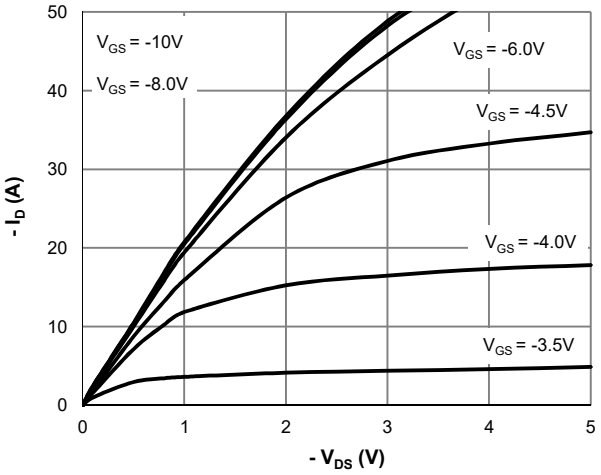


Figure 1: Saturation Characteristics

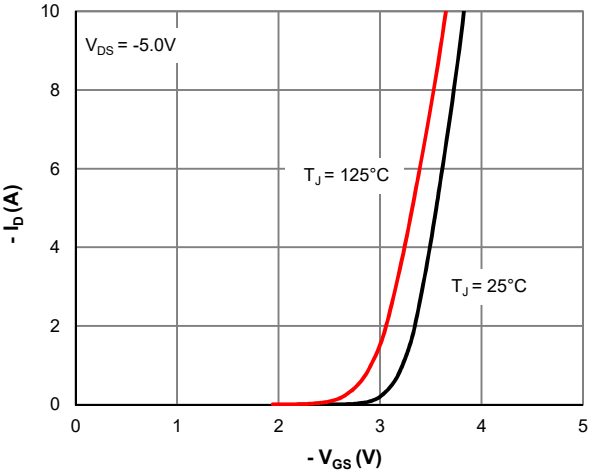


Figure 2: Transfer Characteristics

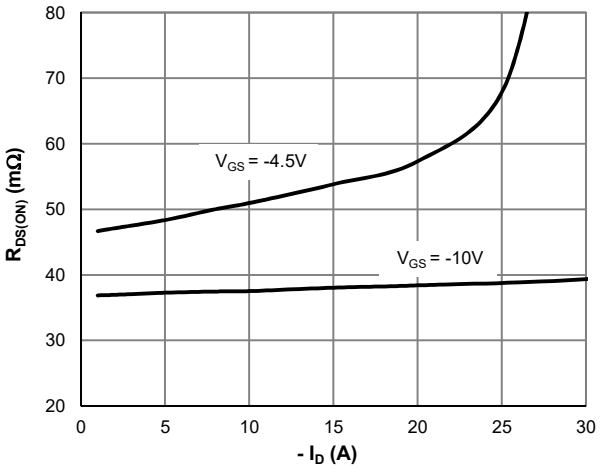


Figure 3: $R_{DS(ON)}$ vs. Drain Current

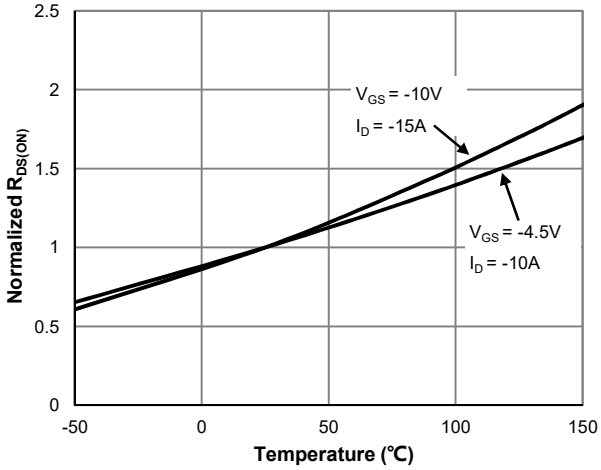


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

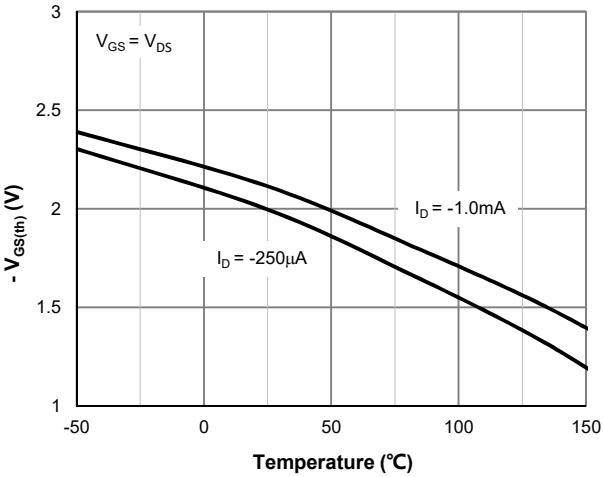


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

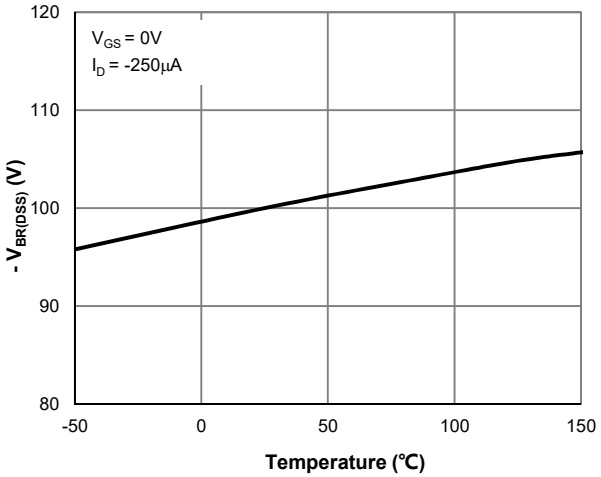


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

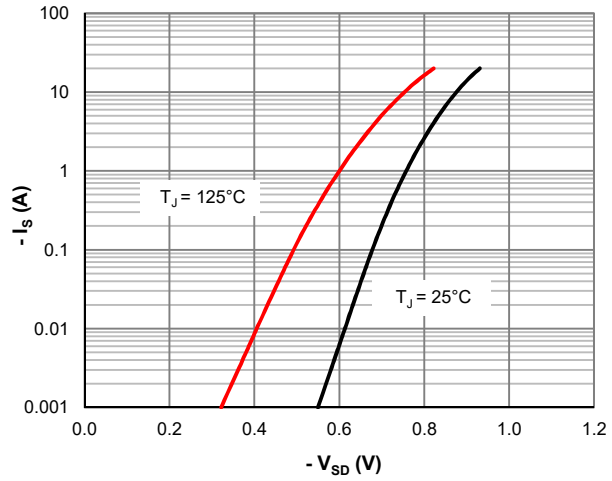


Figure 7: Body-Diode Characteristics

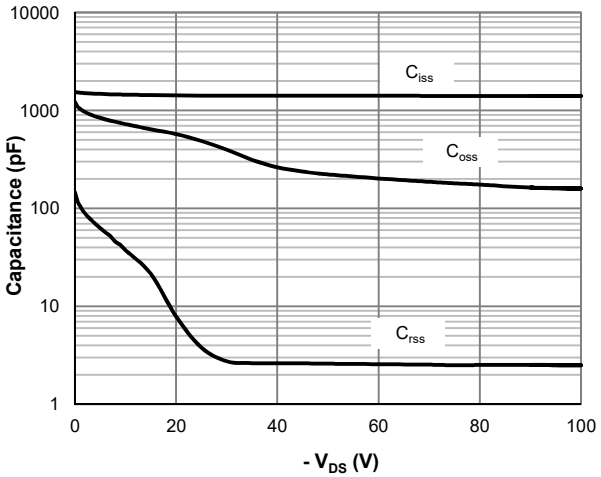


Figure 8: Capacitance Characteristics

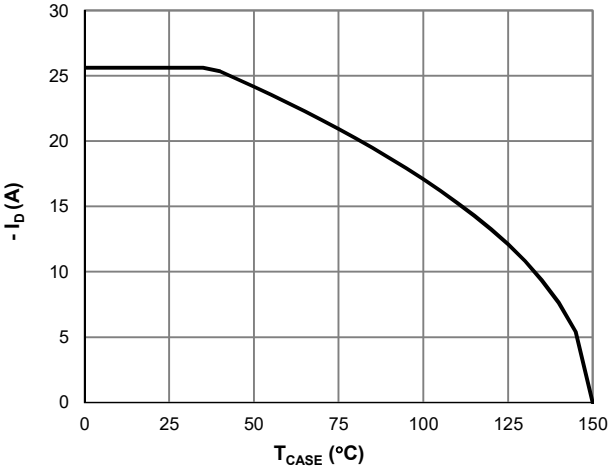


Figure 9: Current De-rating

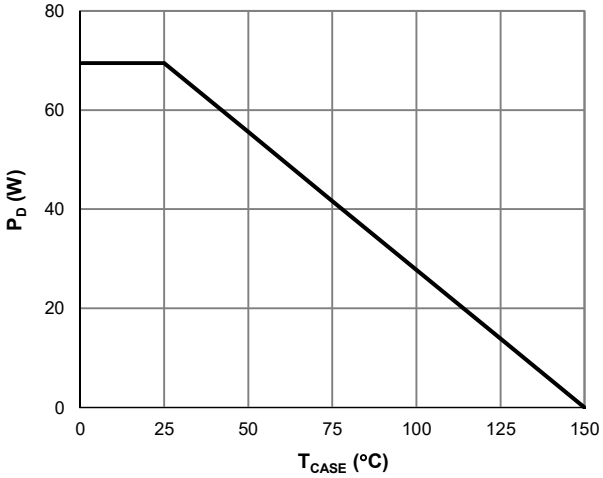


Figure 10: Power De-rating

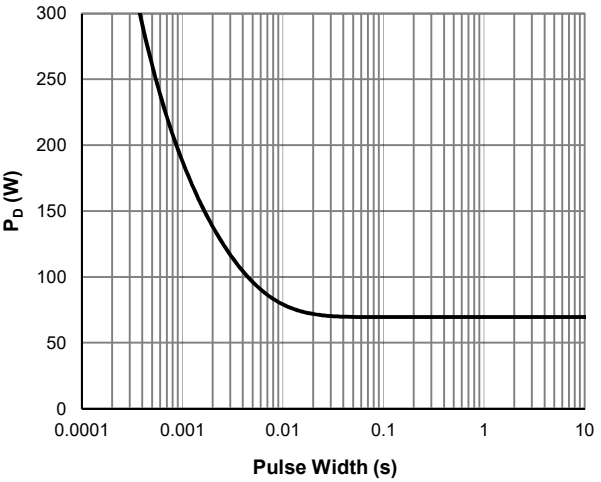


Figure 11: Single Pulse Power Rating, Junction-to-Case

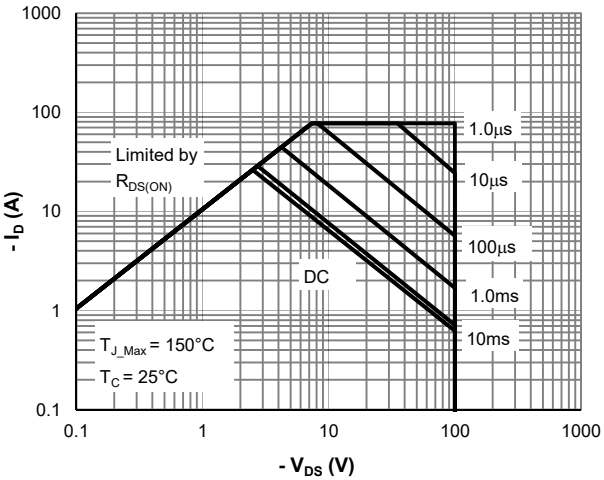


Figure 12: Maximum Safe Operating Area

Typical Electrical & Thermal Characteristics

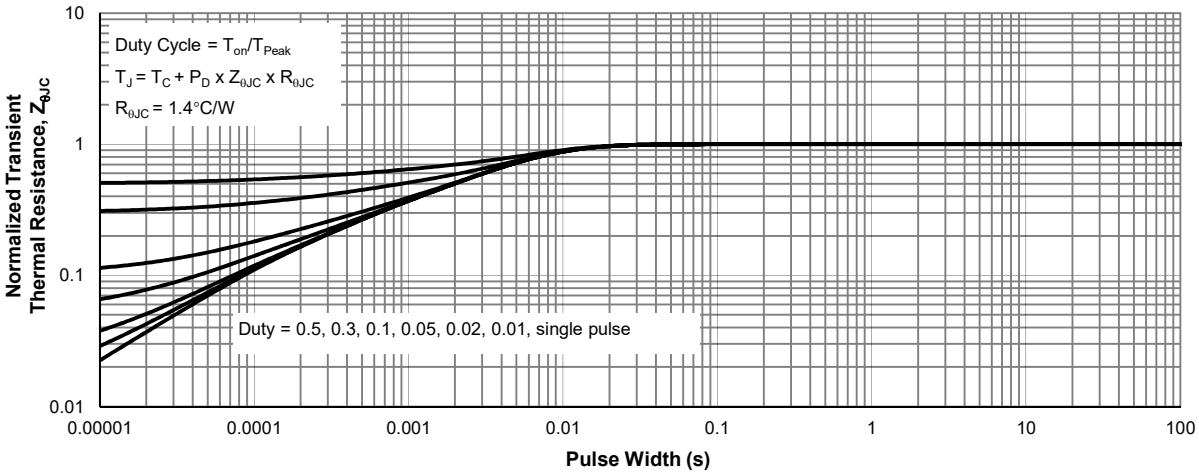
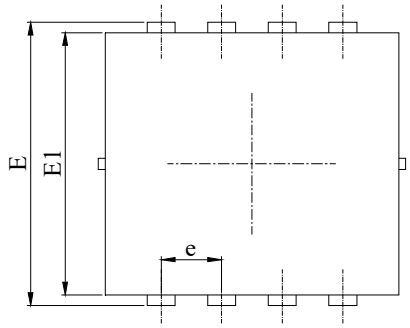


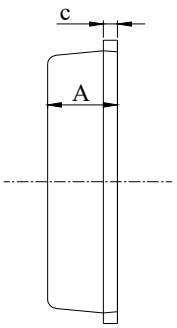
Figure 13: Normalized Maximum Transient Thermal Impedance

PDFN3x3-8L Package Information

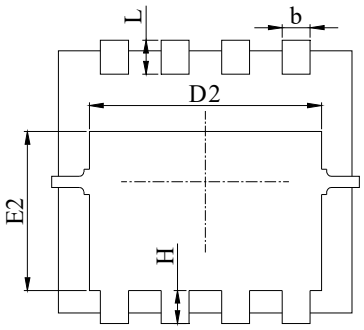
Package Outline



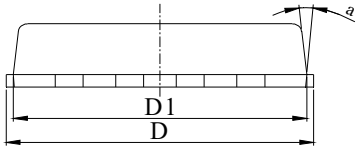
Top View



Side View



Bottom View

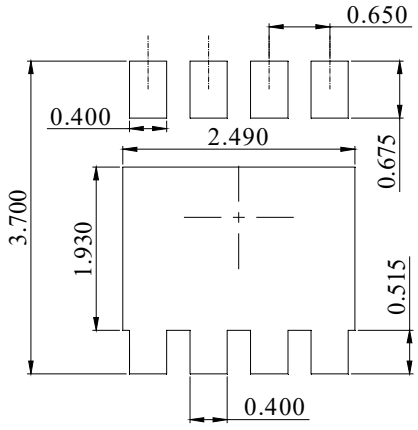


Front View

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS